

MOSFETs Silicon N-Channel MOS (U-MOSIII)

# SSM6N77FU

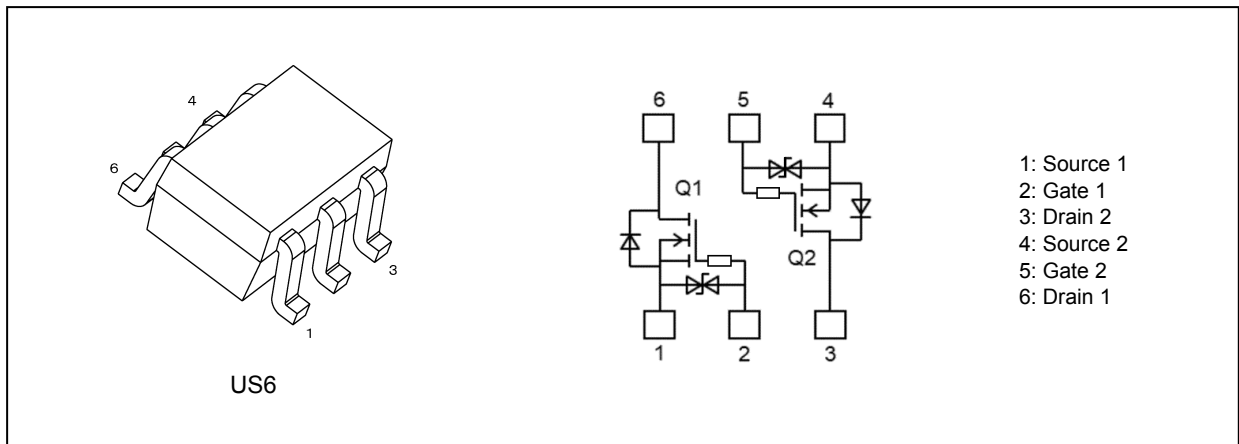
### 1. Applications

- High-Speed Switching
- Analog Switches

### 2. Features

- (1) 1.5 V gate drive voltage.
- (2) Low drain-source on-resistance
  - $R_{DS(ON)} = 5.60 \Omega$  (max) (@ $V_{GS} = 1.5 \text{ V}$ ,  $I_D = 10 \text{ mA}$ )
  - $R_{DS(ON)} = 4.05 \Omega$  (max) (@ $V_{GS} = 1.8 \text{ V}$ ,  $I_D = 20 \text{ mA}$ )
  - $R_{DS(ON)} = 3.02 \Omega$  (max) (@ $V_{GS} = 2.5 \text{ V}$ ,  $I_D = 50 \text{ mA}$ )
  - $R_{DS(ON)} = 2.20 \Omega$  (max) (@ $V_{GS} = 4.5 \text{ V}$ ,  $I_D = 100 \text{ mA}$ )
- (3) Low leakage current
- (4) N-ch 2-in-1

### 3. Packaging and Internal Circuit



Start of commercial production

2024-04

### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ °C}$ ) (Q1,Q2 Common)

| Characteristics                 | Symbol    | Rating     | Unit               |
|---------------------------------|-----------|------------|--------------------|
| Drain-source voltage            | $V_{DSS}$ | 20         | V                  |
| Gate-source voltage             | $V_{GSS}$ | $\pm 10$   |                    |
| Drain current (Note 1)          | $I_D$     | 250        | mA                 |
| Drain current (pulsed) (Note 1) | $I_{DP}$  | 500        |                    |
| Power dissipation (Note 2)      | $P_D$     | 300        | mW                 |
| Channel temperature             | $T_{ch}$  | 150        | $^{\circ}\text{C}$ |
| Storage temperature             | $T_{stg}$ | -55 to 150 | $^{\circ}\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed  $150\text{ °C}$ .

Note 2: Device mounted on an FR4 board. ( $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ mm}$ , Cu pad:  $0.32\text{ mm}^2 \times 6$ )

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

| Characteristics                         | Symbol        | Test Condition                                  | Min  | Typ. | Max        | Unit          |
|---|---------------|---|------|------|------------|---------------|
| Gate leakage current                    | $I_{GSS}$     | $V_{GS} = \pm 5\text{ V}, V_{DS} = 0\text{ V}$  | —    | —    | $\pm 0.08$ | $\mu\text{A}$ |
|   |               | $V_{GS} = \pm 10\text{ V}, V_{DS} = 0\text{ V}$ | —    | —    | $\pm 1$    |               |
| Drain cut-off current                   | $I_{DSS}$     | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$     | —    | —    | 0.08       | V             |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$ | $I_D = 1\text{ mA}, V_{GS} = 0\text{ V}$        | 20   | —    | —          |               |
| Drain-source breakdown voltage (Note 1) | $V_{(BR)DSX}$ | $I_D = 1\text{ mA}, V_{GS} = -10\text{ V}$      | 12   | —    | —          |               |
| Gate threshold voltage (Note 2)         | $V_{th}$      | $V_{DS} = 3\text{ V}, I_D = 1\text{ mA}$        | 0.35 | —    | 1.0        |               |
| Drain-source on-resistance (Note 3)     | $R_{DS(ON)}$  | $I_D = 100\text{ mA}, V_{GS} = 4.5\text{ V}$    | —    | 1.65 | 2.20       | $\Omega$      |
|   |               | $I_D = 50\text{ mA}, V_{GS} = 2.5\text{ V}$     | —    | 2.16 | 3.02       |               |
|   |               | $I_D = 20\text{ mA}, V_{GS} = 1.8\text{ V}$     | —    | 2.66 | 4.05       |               |
|   |               | $I_D = 10\text{ mA}, V_{GS} = 1.5\text{ V}$     | —    | 3.07 | 5.60       |               |
| Forward transfer admittance (Note 3)    | $ Y_{fs} $    | $V_{DS} = 3\text{ V}, I_D = 100\text{ mA}$      | 0.14 | 0.28 | —          | S             |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

| Characteristics                | Symbol    | Test Condition  | Min | Typ. | Max | Unit        |
|--------------------------------|-----------|---|-----|------|-----|-------------|
| Input capacitance              | $C_{iss}$ | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1\text{ MHz}$  | —   | 12   | —   | $\text{pF}$ |
| Reverse transfer capacitance   | $C_{rss}$ |   | —   | 4.1  | —   |             |
| Output capacitance             | $C_{oss}$ |   | —   | 5.5  | —   |             |
| Switching time (turn-on time)  | $t_{on}$  | $V_{DD} = 10\text{ V}, I_D = 100\text{ mA},$<br>$V_{GS} = 0\text{ to }2.5\text{ V}, R_{GS} = 50\ \Omega$<br>Common source, See Chapter 5.3. | —   | 18   | —   | ns          |
| Switching time (turn-off time) | $t_{off}$ |   | —   | 36   | —   |             |

#### 5.3. Switching Time Test Circuit(Q1,Q2 Common)

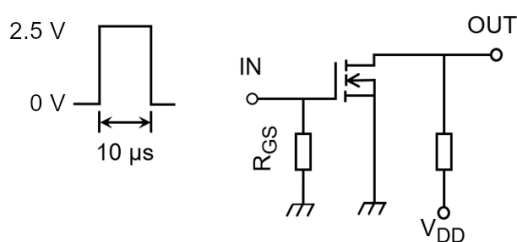


Fig. 5.3.1 Switching Time Test Circuit

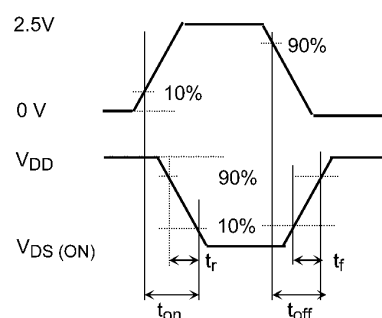


Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$ ) (Q1,Q2 Common)

| Characteristics                | Symbol    | Test Condition                              | Min | Typ. | Max  | Unit |
|--------------------------------|-----------|---|-----|------|------|------|
| Diode forward voltage (Note 1) | $V_{DSF}$ | $I_D = -250\text{ mA}, V_{GS} = 0\text{ V}$ | —   | -0.9 | -1.2 | V    |

Note 1: Pulse measurement.

## 6. Marking

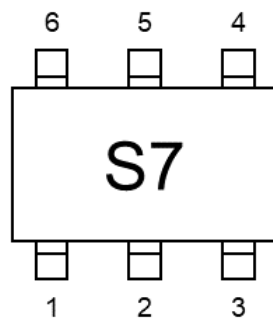


Fig. 6.1 Marking

### 7. Characteristics Curves (Note)

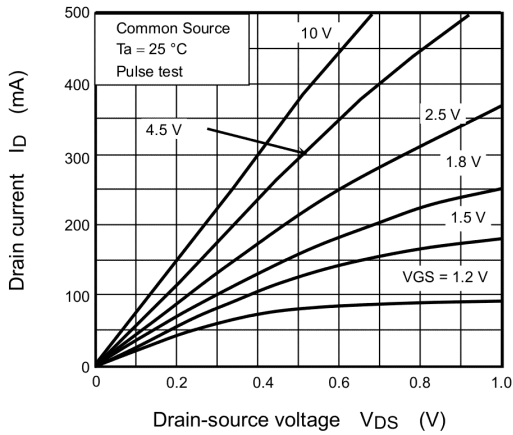


Fig. 7.1 ID - VDS

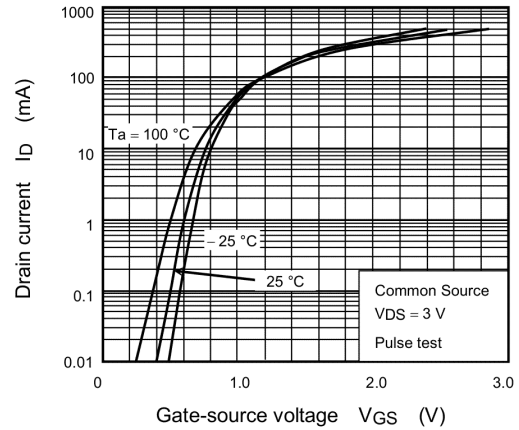


Fig. 7.2 ID - VGS

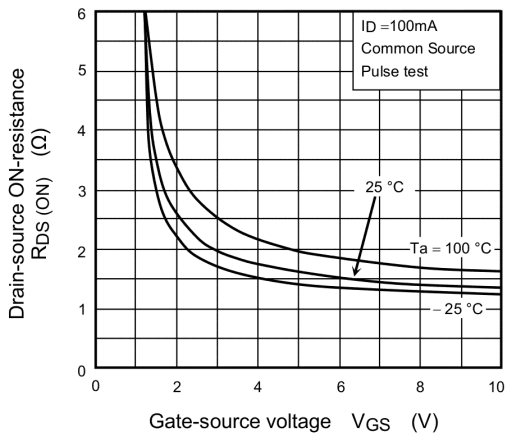


Fig. 7.3 RDS(ON) - VGS

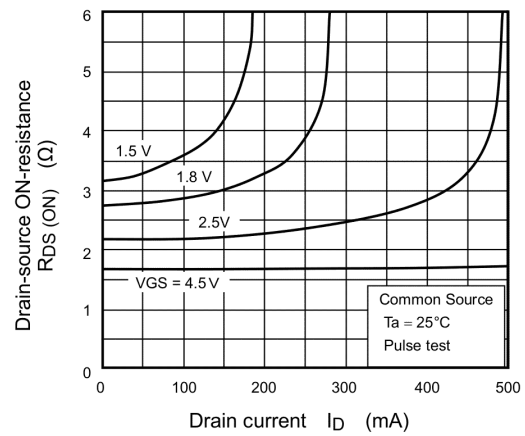


Fig. 7.4 RDS(ON) - ID

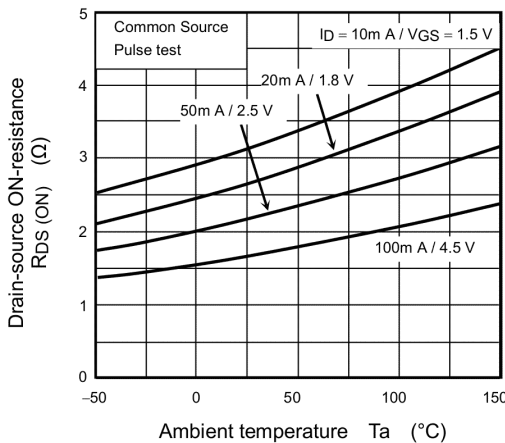


Fig. 7.5 RDS(ON) - Ta

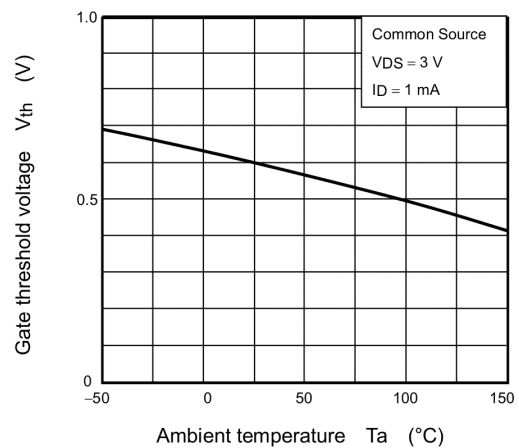
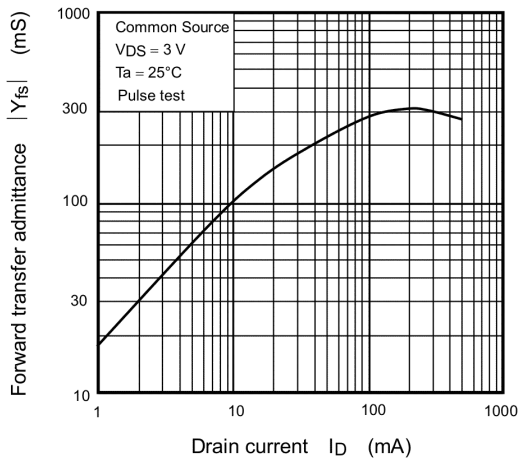
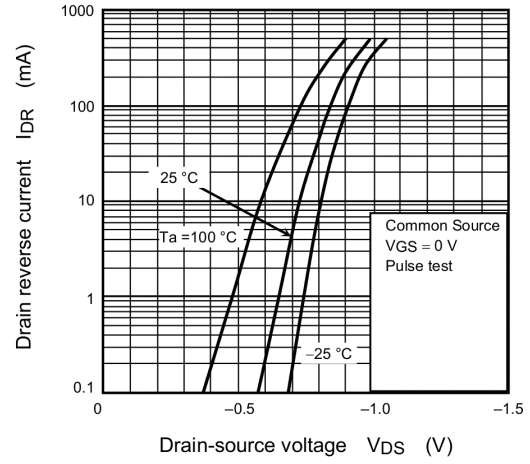


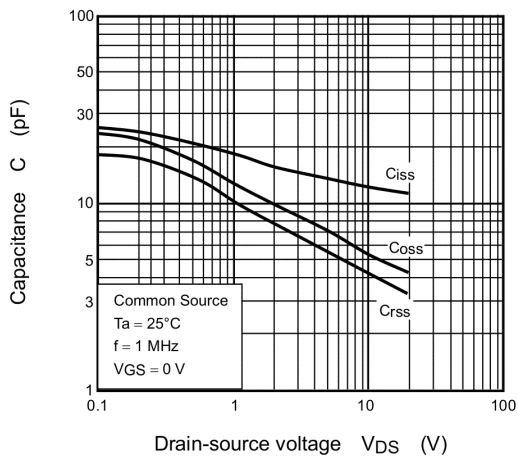
Fig. 7.6 Vth - Ta



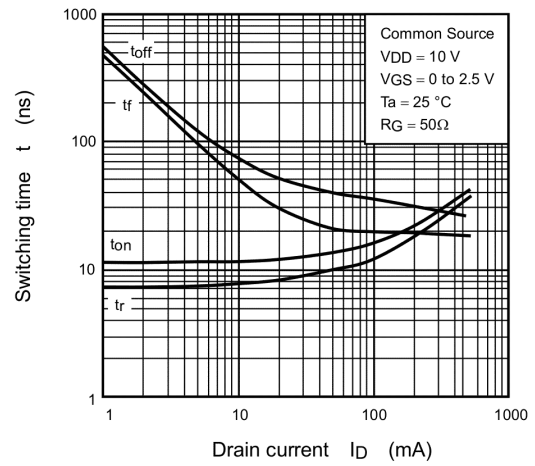
**Fig. 7.7**  $|Y_{fs}| - I_D$



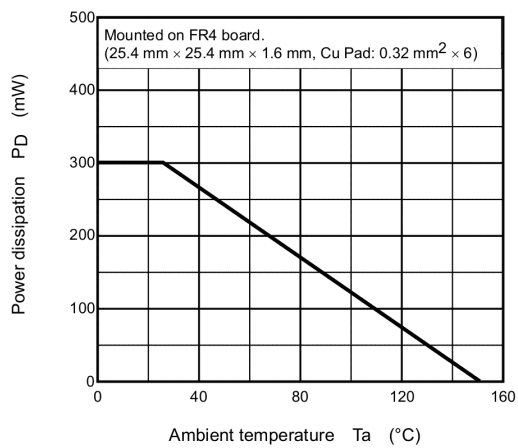
**Fig. 7.8**  $I_{DR} - V_{DS}$



**Fig. 7.9**  $C - V_{DS}$



**Fig. 7.10**  $t - I_D$

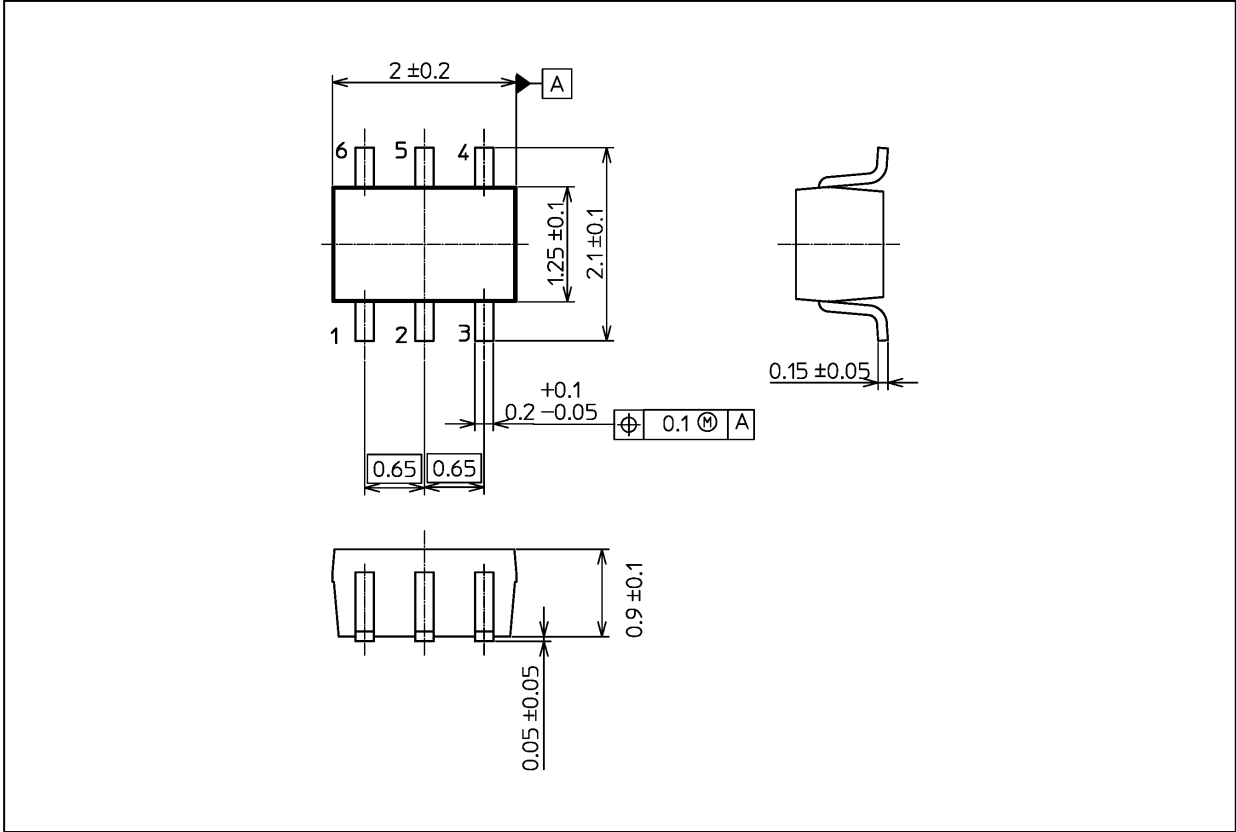


**Fig. 7.11**  $P_D - T_a$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 6.8 mg (typ.)

|                 |
|-----------------|
| Package Name(s) |
| Nickname: US6   |

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